

Effect of counter ions on the reduction process of Sm^{3+} ions in $\text{TiO}_2\text{-ZrO}_2\text{-Al}_2\text{O}_3\text{-SiO}_2$ glasses

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Abstract

The radio-chemical reaction of Sm^{3+} reduction in $x\text{TiO}_2(\text{ZrO}_2)-(10-x)\text{Al}_2\text{O}_3-90\text{SiO}_2$ glasses ($x=0-10$ mol%) was examined by a photoluminescence technique with fluorescence intensities at 560–650 nm (Sm^{3+} ; ${}^4\text{G}_{5/2} \rightarrow {}^6\text{H}_J$) and 680–720 nm (Sm^{2+} ; ${}^5\text{D}_0 \rightarrow {}^7\text{F}_J$). It was found that the reduction of Sm^{3+} ions by X-ray irradiation was significantly decreased by the introduction of TiO_2 and no reduction occurred in the glasses containing TiO_2 above 5%. On the other hand, in the ZrO_2 containing glasses, the reduction of Sm^{3+} ions was almost monotonous up to 5% of ZrO_2 . Electron spin resonance (ESR) spectra revealed the presence of some defect centers; hole-trap center (HTC) and electron-trap center (ETC). Hole centers trapped by oxygen ions bound to the Al^{3+} ions were strongly related to the reduction process from Sm^{3+} to Sm^{2+} ions; the released electrons from the Al-related HTC were captured by the nearest Sm^{3+} ions, forming Sm^{2+} . On the other hand, in the TiO_2 -containing glasses, electrons generated were preferably trapped in Ti^{4+} ions so as to form ETC, resulting in no reduction of Sm^{3+} ions. © 2005 Elsevier B.V. All rights reserved.

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1. Introduction

Rare-earth ions-doped glasses have widely been studied because of their unique optical properties and applications for opto-telecommunication, such as laser action, upconversion, amplifier and spectral hole burning [1,2]. Persistent spectral hole burning (PSHB) phenomena are especially interesting due to its application to frequency-domain optical data storage. Glasses are more preferred as a host matrix of rare-earth ions for their inhomogeneously broadened line width of optical transitions, facile compositional variation and easy mass production. Recently, using a sol-gel technique, we prepared Sm^{2+} ions-doped aluminosilicate glasses and demonstrated the PSHB up to room temperature [3–5]. Spectral holes are considered to be burnt by photoinduced chemical reactions within the rare-earth ions or between the rare-earth and matrix glass structure [6].

So far, we have investigated the reduction of Sm^{3+} into Sm^{2+} ions by X-ray or femtosecond laser irradiation and

the formation of the PSHB. These glasses give faster and more efficient hole burning compared to the H_2 -gas treated glasses [3–5]. It was also noted that in the glasses irradiated with X-ray there were an amount of aluminium-oxygen hole centers (Al-OHC), which were hole centers trapped with oxygen bounded to the Al ions, and the generated quantity were closely correlated with the quantity of Sm^{3+} reduction [7].

In this study, a X-ray reduction process of Sm^{3+} ions in $\text{TiO}_2(\text{ZrO}_2)\text{-Al}_2\text{O}_3\text{-SiO}_2$ glasses was investigated in relation with various point defects generated in each of these glasses.

2. Experiments

2.1. Sample preparation

$x\text{TiO}_2$ (or ZrO_2)-(10-x) Al_2O_3 -90 SiO_2 (mol%) glasses doped with 10 wt% Sm_2O_3 were prepared by the sol-gel process of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Al}(\text{OC}_4\text{H}_9)_3$, $\text{Ti}(\text{OC}_3\text{H}_7)_4$, $\text{Zr}(\text{OC}_3\text{H}_7)_4$

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and $\text{SmCl}_3 \cdot 6\text{H}_2\text{O}$. Gels were synthesized through hydrolysis of the mixed materials in ethanol, a detailed explanation of which is given elsewhere [8,9]. The gels were heated in air at $40^\circ\text{C}/\text{h}$ to 800°C and held at that temperature for 2 h. Some of the glasses were irradiated with X-rays. The X-ray irradiation was performed by the $\text{Cu K}\alpha$ line for 14 h at room temperature with 40 kV and 20 mA using a conventional X-ray diffractometer (Rigaku RAD-B system).

2.2. Measurement of properties

The fluorescence spectra were recorded at right angles using a Hamamatsu, R955 photomultiplier. A xenon lamp passed through a monochromator for excitation. Electron spin resonance (ESR) measurement was performed using a Jasco, JES-FE 1XG spectrometer at 77 K. The g -values and the quantities of spin obtained ESR signals were calibrated by the utilization of diphenylpicrylhydrazal (DPPH) and 2,2,6,6-tetramethyl-1-piperidinyloxy (TEMPO), respectively.

3. Results and discussion

3.1. Reduction of samarium ions in glasses

Fig. 1 shows the fluorescence spectra of Sm^{3+} ion doped $10\text{Al}_2\text{O}_3\text{-}90\text{SiO}_2$ glasses before and after X-ray irradiation. The sharp fluorescence lines observed around 565, 600 and 650 nm before the irradiation are ascribed to $^4\text{G}_{5/2}\text{-}^6\text{H}_{5/2,7/2,9/2}$ transitions, respectively, of the Sm^{3+} ions. After the irradiation, new fluorescence lines noticeably emerges around 680, 700 and 720 nm. These bands are characteristic bands of Sm^{2+} ions arising from $^5\text{D}_{0,1,2}$ transitions, respectively. For evaluating the variation of the

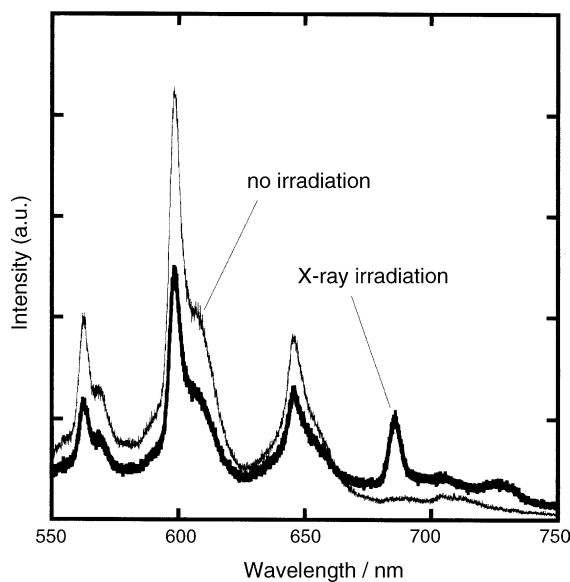


Fig. 1. Fluorescence spectra of Sm^{3+} -doped $\text{Al}_2\text{O}_3\text{-SiO}_2$ glass before and after X-ray irradiation ($\lambda_{\text{ex}} = 404 \text{ nm}$).

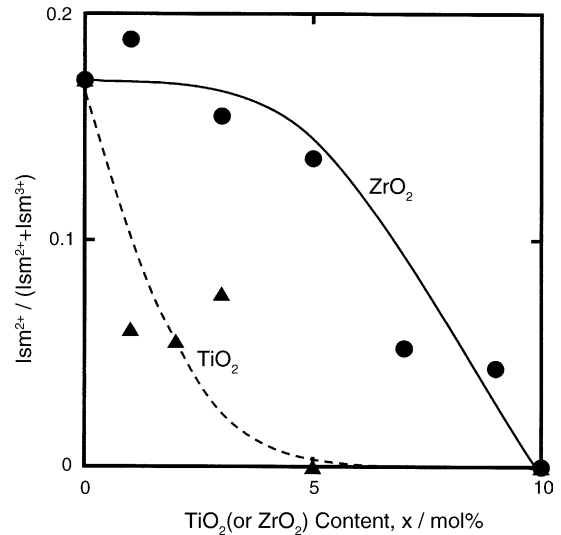


Fig. 2. The variation of the reduction of Sm^{3+} ions in different matrices.

reduction of Sm^{3+} ions with the substitution of Al_2O_3 with $\text{TiO}_2(\text{ZrO}_2)$, the fluorescence intensity ratio of the Sm^{2+} ions, $I_{\text{Sm}^{2+}} / (I_{\text{Sm}^{2+}} + I_{\text{Sm}^{3+}})$, is shown in Fig. 2, where $I_{\text{Sm}^{2+}}$ is the fluorescence intensity of Sm^{2+} ions and $I_{\text{Sm}^{3+}}$ is that of Sm^{3+} ions. In case of the substitution by TiO_2 , the fluorescence intensity ratio drastically decreases, and no reduction occurs in the glasses containing TiO_2 above 5%. On the other hand, in the case of ZrO_2 , the ratio is almost monotonous up to 5% of ZrO_2 , then the fluorescence of Sm^{2+} ions disappears when Al_2O_3 is reached to 0%.

3.2. Generation of point defects in glasses

Fig. 3 shows ESR spectra of the glasses irradiated with X-ray. In $10\text{Al}_2\text{O}_3\text{-}90\text{SiO}_2$ glass, there is one signal of defects

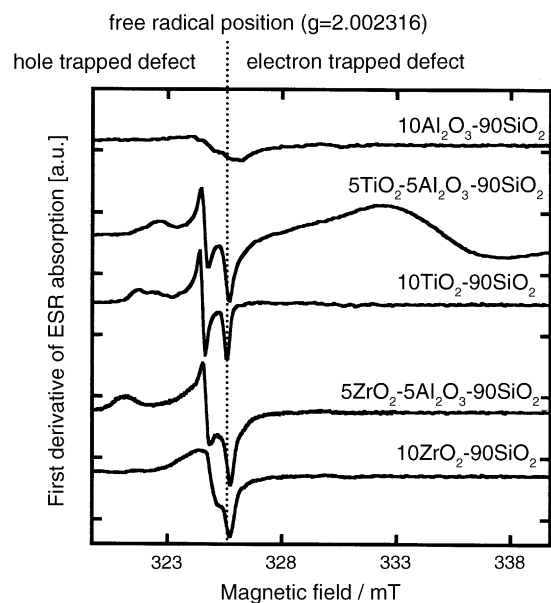


Fig. 3. ESR spectra of the glasses irradiated with X-ray irradiation.

Table 1
The quantities of hole- or electron-trap centers

Composition	HTC (spin/g)	ETC (spin/g)
10Al ₂ O ₃ –90SiO ₂	3.8×10^{16}	None
5TiO ₂ –5Al ₂ O ₃ –90SiO ₂	3.9×10^{16}	3.6×10^{17}
10TiO ₂ –90SiO ₂	2.3×10^{16}	None
5ZrO ₂ –5Al ₂ O ₃ –90SiO ₂	2.4×10^{16}	None
10ZrO ₂ –90SiO ₂	4.3×10^{16}	None

with magnetic anisotropy in the glass. It is defined as hole-trap centers trapped by the oxygen ions bound to Al³⁺ ions (Al–OHC: $g=2.0075$) [7]. The defects which are generated with cutting of Al-related bonding are more effective about the reduction of Sm³⁺ ions, because Sm ions tend to exist near to Al [7,10]. Thus, Sm³⁺ ions experience no reduction by X-ray when Al₂O₃ is not one of the glass components (see Fig. 2). In the other glasses, they have each hole-trap center with different g -value. Furthermore, only in the glass containing TiO₂, Al₂O₃ and SiO₂, electron-trap centers are clearly observed. With three component glasses contained Al₂O₃, SiO₂ and TiO₂, the quantity of reduction of Sm³⁺ ions was exceedingly small (see Fig. 2). This suggests that Sm³⁺ ions cannot be supplied with electrons in such glasses because electron-trapped centers are attracting them strongly.

Table 1 summarizes the quantities of hole- or electron-trapped defects generated by X-ray (see also Fig. 3). In 5TiO₂–5Al₂O₃–90SiO₂ glass, electron-trap centers of 3.6×10^{17} spin/g are generated, which are by 10 times more than hole-trap centers. It is found that the electron-trap centers are generated enough to prevent the reduction of Sm³⁺ ions. For this reason, the fluorescence intensity ratio about Sm²⁺ ions was very small in the aluminosilicate based glasses in which TiO₂ was added.

4. Conclusions

We studied the reduction process of Sm³⁺ ions and generation of defects with X-ray irradiation in x TiO₂ (or ZrO₂)–(10– x)Al₂O₃–90SiO₂ glasses. In the glasses not containing Al₂O₃, no reduction of Sm³⁺ ions occurred because the reduction process of Sm³⁺ ions closely correlated with Al–OHC. On the other hand, in case of three component glasses containing Al₂O₃, SiO₂ and TiO₂, the Sm³⁺ ions were hardly reduced with X-ray irradiation. This suggested that electron-trap centers generated in the glass matrix were attracting electrons strongly. Therefore, Sm³⁺ ions were not supplied with electrons required for reduction.

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